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LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Kentaro NAKAJIMA, et al.

FILING DATE

September 12, 2003

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DM	AA	5,940,319	08/17/1999	M. DURLAM, et al.			
DM	AB	5,956,267	09/21/1999	A. T. HURST, et al.			
DM	AC	5,946,228	08/31/1999	D. W. ABRAHAM, et al.			
DM	AD	6,072,718	06/06/2000	D. W. ABRAHAM, et al.			
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DM	AF	6,005,800	12/21/1999	R. H. KOCH, et al.			
DM	AG	6,081,445	06/27/2000	J. SHI, et al.			
DM	AH	6,134,139	10/17/2000	M. K. BHATTACHARYA, et al.			
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
DM	AO	WO 001/10172	02/24/2000	WIPO (with English Abstract and corr. JP 2002-522915)		X
DM	AP	2002-522915	07/23/2002	JAPAN		X
DM	AQ	8-306014	11/22/1996	JAPAN (with English Abstract)		X
	AR					
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

DM	AV	S. TEHRANI, et al., Journal of Applied Physics, Magnetoresistive Magnetic Random Access Memory, vol. 85, no. 8, pages 5822-5827, "HIGH DENSITY SUBMICRON MAGNETORESISTIVE RANDOM ACCESS MEMORY (INVITED)", April 15, 1999	
DM	AW	R. SCHEUERLEIN, et al., IEEE International Solid-State Circuits Conference, ISSCC 2000 / Session 7 / TD: Emerging Memory & Device Technologies / Paper TA 7.2, pages 128-129, "A 10ns READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL", February 8, 2000	
DM	AX	M. SATO, et al., IEEE Transactions on Magnetics, vol. 33, no. 5, pages 3553-3555, "SPIN-VALVE-LIKE PROPERTIES AND ANNEALING EFFECT IN FERROMAGNETIC TUNNEL JUNCTIONS", September 1997	
DM	AY	M. SATO, et al., Jpn. J. Appl. Phys, vol. 36, part 2, no. 2B, pages L 200-L 201, "SPIN-VALVE-LIKE PROPERTIES OF FERROMAGNETIC TUNNEL JUNCTIONS", February 15, 1997	
DM	AZ	K. INOMATA, et al., Jpn. J. Appl. Phys, vol. 36, part 2, no. 10B, pages L 1380-L 1383, "SPIN-DEPENDENT TUNNELING BETWEEN A SOFT FERROMAGNETIC LAYER AND HARD MAGNETIC NANOSIZE PARTICLES", October 15, 1997	<input type="checkbox"/> Additional References sheet(s) attached

Examiner

Date Considered

6/8/05

*Examiner: Initial if reference is considered. Whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.